NSN 5961-01-306-7100

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-306-7100 **Inclosure Material:** Ceramic **Overall Length:** 0.785 inches **Overall Height:** 0.200 inches **Overall Width:** 0.300 inches **End Application:** Inertial measuring unit **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 35.0 breakdown voltage, drain-to-source, with all other terminals short-circuited to source all transistor **Current Rating Per Characteristic:** 3.00 amperes drain current all transistor **Power Rating Per Characteristic:** 4.0 watts total device dissipation all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Test Data Document:** 06481-932545 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 14 printed circuit Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: